

ABSTRACTDYNAMIC THRESHOLD VOLTAGE MOS TRANSISTOR FITTED  
WITH A CURRENT LIMITER, AND PROCESS FOR MAKING SUCH A  
TRANSISTOR

The invention concerns a semi-conductor device comprising on a substrate:

- a first dynamic threshold voltage MOS transistor (10), with a gate (116), and a channel (111) of a first conductivity type, and

- a current limiter means (20) connected between the gate and the channel of said first transistor.

In accordance with the invention, this first transistor is fitted with a first doped zone (160) of the first conductivity type, connected to the channel, and the current limiter means comprises a second doped zone (124) of a second conductivity type, placed against the first doped zone and electrically connected to the first zone by an ohmic connection.

Application to the manufacture of CMOS circuits.

Figure 4.